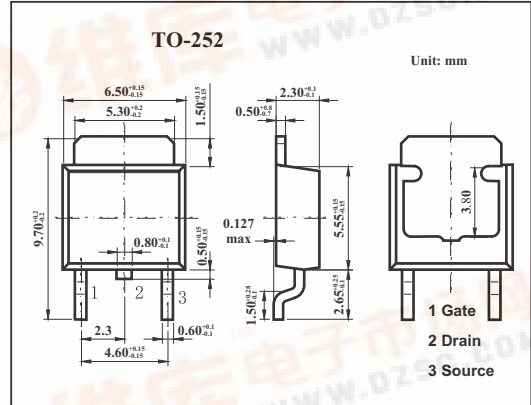
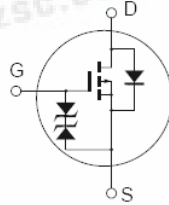


SMD Type MOSFET

Silicon P-Channel MOSFET
2SJ319S

Features

- Low on-state resistance
RDS(on)=2.3 Ω (VGS=-10V, ID=-2A)
- High speed switching



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	-200	V
Gate to source voltage	V _{GSS}	±20	V
Drain current (DC)	I _D	-3	A
Drain current(pulse) *	I _D	-12	A
Power dissipation	P _D	20	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs; d ≤ 1%.

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain to source breakdown voltage	V _{DSS}	I _D =-10mA, V _{GS} =0	-200			V
Gate to source breakdown voltage	V _{GSS}	I _G =±100 μA, V _{DS} =0	±20			V
Drain cut-off current	I _{DSS}	V _{DS} =-160V, V _{GS} =0			-100	μA
Gate leakage current	I _{GSS}	V _{GS} =±16V, V _{DS} =0			±10	μA
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-2.0		-4.0	V
Forward transfer admittance	Y _{fs}	V _{DS} =-10V, I _D =-2A	1.0	1.7		S
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-2A		1.7	2.3	Ω
Input capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0, f=1MHZ		330		pF
Output capacitance	C _{oss}				130	pF
Reverse transfer capacitance	C _{rss}				25	pF
Turn-on delay time	t _{d(on)}	V _{GS(on)} =-10V, I _D =-2A RL=15 Ω		10		ns
Rise time	t _r			30		ns
Turn-off delay time	t _{d(off)}			40		ns
Fall time	t _f			30		ns
Body to drain diode forward voltage	V _{DF}	I _F =-3A, V _{GS} =0		-1.15		V
Body to drain diode reverse recovery time	t _{rr}	I _F =-3A, V _{GS} =0, di/dt=50A/μs		180		ns

